



Attorney's Docket No.: 1977-242001 / US3586

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9/17/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ohnuma, et al. Art Unit : 1765
Serial No.: 09/050,182 Examiner : R. Kunemund
Filed : March 26, 1998
Title : METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

Commissioner for Patents
Washington, D.C. 20231

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RESPONSE

In response to the action mailed May 6, 2002, please amend
the application as follows:

In the claims:

Please amend claims 1, 3, 5, 9, 11, 13, 17, 19, 21, 25, 27,
29, 33, 36, 39, 42, 45, 46, 49, 52, 53, 57, and 76-81 as
follows:

5/21/02
D. 1. (Amended) A method of manufacturing a semiconductor
device including at least a thin film transistor, said method
comprising the steps of:

forming an amorphous semiconductor film comprising
silicon over a substrate having an insulating surface;

09/12/2002 MDR/KMH 00000014 09050102

0. FC:003 612.00 OP
02 FC:002 335.00 OP

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this
correspondence is being deposited with the
United States Postal Service as first class mail
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September 6, 2002

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